

CNA1301H

Photo Interrupter

For contactless SW, object detection

Overview

CNA1301H is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

Features

- Ultraminiature : 3.8×4.2 mm (height : 4.2 mm)
- Highly precise position detection : 0.15 mm
- Gap width : 1.4 mm
- Support for thin equipment (permits direct mounting on printed circuit board)

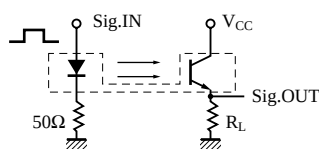
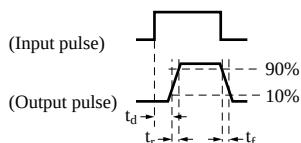
Absolute Maximum Ratings (Ta = 25°C)

	Parameter	Symbol	Ratings	Unit
Input (Light emitting diode)	Reverse voltage (DC)	V_R	6	V
	Forward current (DC)	I_F	50	mA
	Power dissipation	P_D^{*1}	75	mW
Output (Photo transistor)	Collector current	I_C	20	mA
	Collector to emitter voltage	V_{CEO}	35	V
	Emitter to collector voltage	V_{ECO}	6	V
Temperature	Collector power dissipation	P_C^{*2}	75	mW
	Operating ambient temperature	T_{opr}	-25 to +85	°C
	Storage temperature	T_{stg}	-40 to +100	°C

Electrical Characteristics (Ta = 25°C)

	Parameter	Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	V_F	$I_F = 20\text{mA}$		1.2	1.4	V
	Reverse current (DC)	I_R	$V_R = 3\text{V}$			10	μA
Output characteristics	Collector cutoff current	I_{CEO}	$V_{CE} = 20\text{V}$			100	nA
Transfer characteristics	Collector current	I_C	$V_{CE} = 5\text{V}, I_F = 5\text{mA}$	100		1300	μA
	Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_F = 10\text{mA}, I_C = 40\mu\text{A}$			0.4	V
	Response time	t_r, t_f^*	$V_{CC} = 5\text{V}, I_C = 0.1\text{mA}, R_L = 1000\Omega$		35		μs

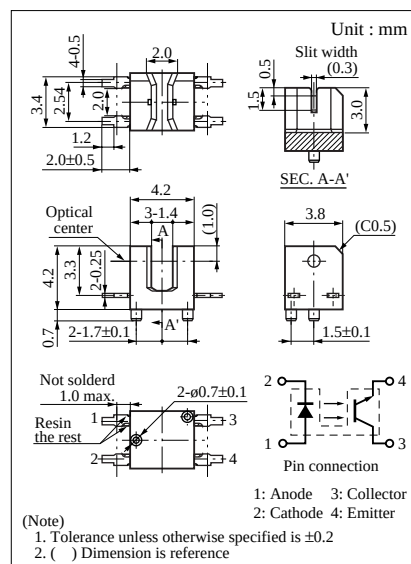
* Switching time measurement circuit



t_d : Delay time

t_r : Rise time (Time required for the collector current to increase from 10% to 90% of its final value)

t_f : Fall time (Time required for the collector current to decrease from 90% to 10% of its initial value)



*¹ Input power derating ratio is 1.0 mW/°C at Ta ≥ 25°C.

*² Output power derating ratio is 1.0 mW/°C at Ta ≥ 25°C.

